# **ECE-656: Fall 2009**

# Lecture 1: Bandstructure Review

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## outline

- 1) Bandstructure in bulk semiconductors
- 2) Quantum confinement
- 3) Summary

#### electrons in solids

#### Hydrogen atom:

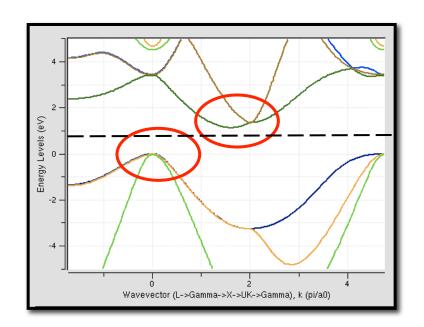
$$-\frac{\hbar^2}{2m_0}\nabla^2\psi(\vec{r}) + U(\vec{r})\psi(\vec{r}) = E\psi(\vec{r}) \qquad U(\vec{r}) = -\frac{q^2}{4\pi\varepsilon_0 r}$$

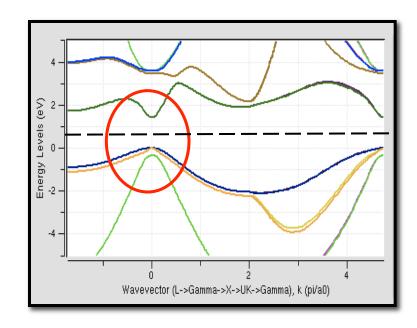
### Crystals:

# energy bands

For any wavevector, k, there is an infinite set of eigenenergies,  $E_n(\vec{k})$  'bandstructure'

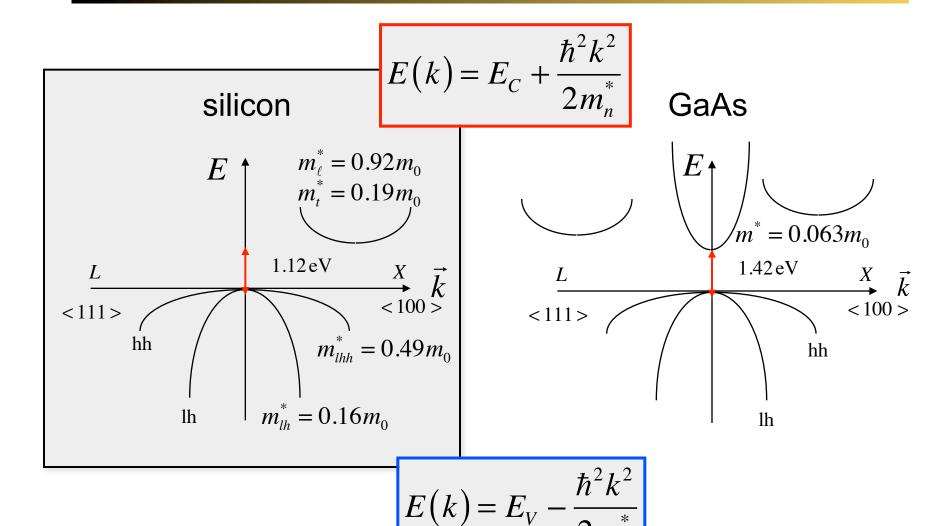
#### silicon



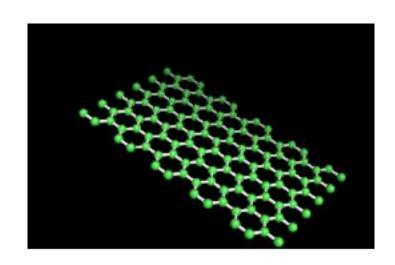


('Bandstructure Lab' at www.nanoHUB.org)

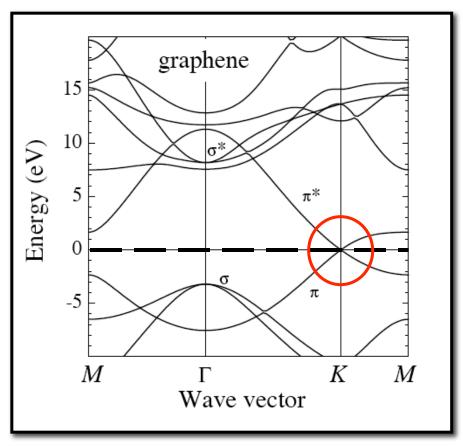
## model bandstructure



# bandstructure of graphene



(CNTBands on www.nanoHUB.org)

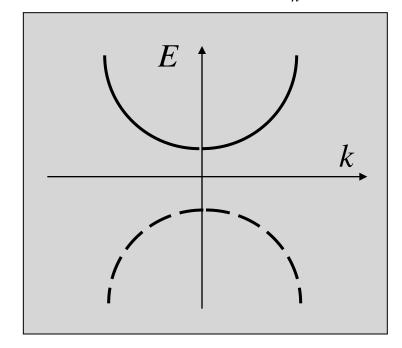


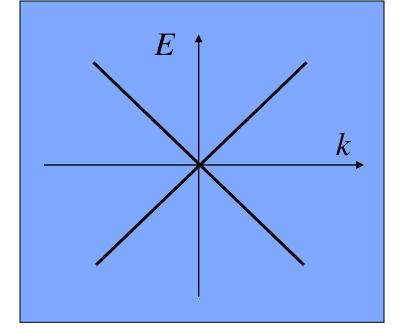
http://www.szfki.hu/~kamaras/nanoseminar/Reich\_Stephanie-85-100.pdf

# E(k) for these lectures

$$E(k) = E_C + \frac{\hbar^2 k^2}{2m_n^*}$$

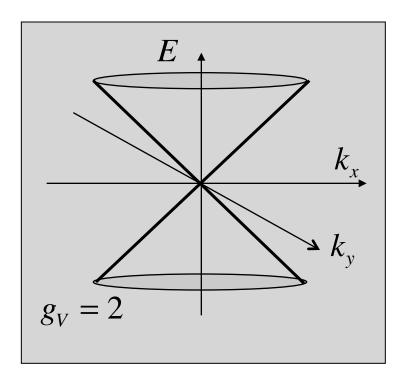
$$E(k) = \pm \hbar v_F k$$





$$E(k) = E_V - \frac{\hbar^2 k^2}{2m_p^*}$$

# E(k) for graphene



$$E(k) = \pm \hbar \upsilon_F \sqrt{k_x^2 + k_y^2} = \pm \hbar \upsilon_F k$$

#### Recall:

$$v_g(\vec{k}) = \frac{1}{\hbar} \frac{dE(k)}{dk}$$

### For graphene:

$$v_g(\vec{k}) = v_F$$

#### Also recall:

$$m^* = \left(\frac{1}{\hbar^2} \frac{d^2 E(k)}{d^2 k}\right)^{-1}$$

## For graphene:

$$m^* = ?$$

## effective mass for graphene

#### Mobility:

$$\mu = \frac{q\tau}{m^*}$$

For graphene:

$$\mu = ?$$

As long as we have an E(k), we have everything we need. There is no need to ask what the effective mass is (but it sometimes can be useful to think in terms of an effective mass).

## electronic structure of graphene

For a more thorough, but introductory treatment of bandstructure, see the nanoHUB lectures of Prof. Supriyo Datta:

ECE 495N: Fundamentals of Nanoelectronics

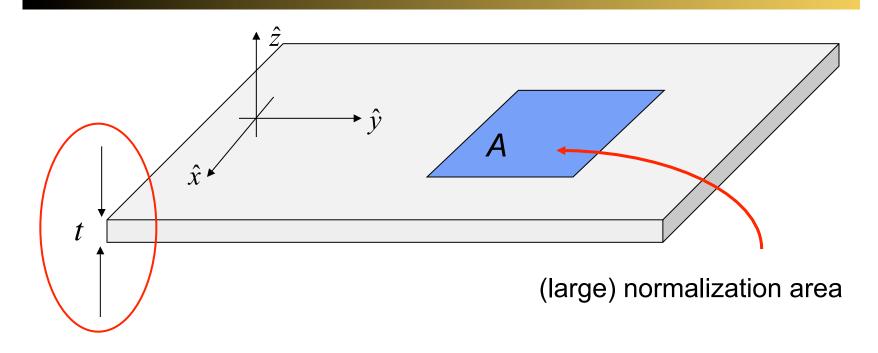
Lecture 18-21: Bandstructure – I, II, III, and graphene

http://nanohub.org/courses/fundamentals\_of\_nanoelectronics

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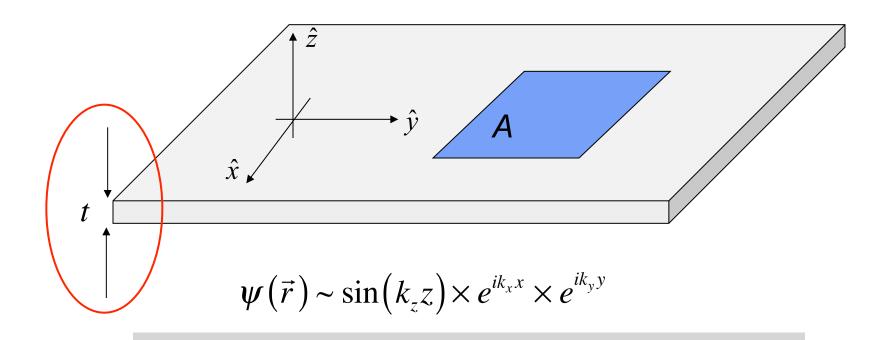
## two-dimensional electrons



Semi-infinite in the x-y plane, but very thin in the z-direction.

$$\psi(\vec{r}) \sim e^{i\vec{k}\cdot\vec{r}} \rightarrow \sin(k_z z) \times e^{ik_x x} \times e^{ik_y y}$$

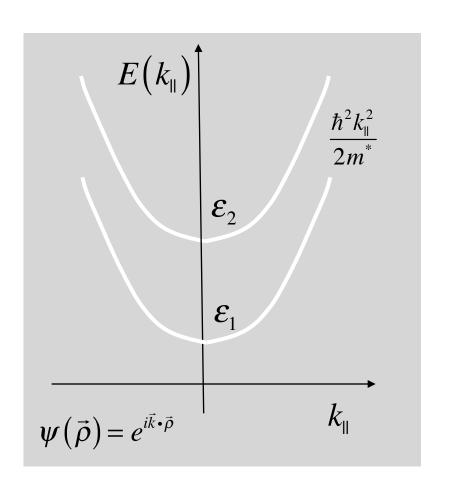
## 2D electrons: subbands



$$\psi(z=0) = \psi(z=t) = 0$$

$$k_z t = j\pi \qquad k_z = \frac{j\pi}{t} \qquad \varepsilon_j = \frac{\hbar^2 j^2 \pi^2}{2m^* t^2}$$

## subbands

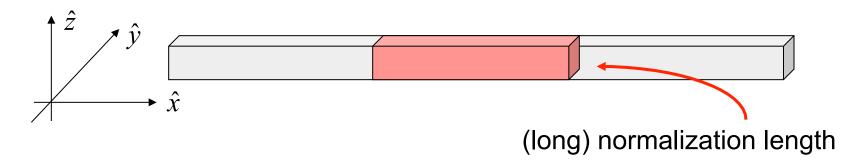


$$\varepsilon_j = \frac{\hbar^2 j^2 \pi^2}{2m^* t^2}$$

$$k_{\parallel} = \sqrt{k_x^2 + k_y^2}$$

$$E = \varepsilon_j + \frac{\hbar^2 k_{\parallel}^2}{2m^*}$$

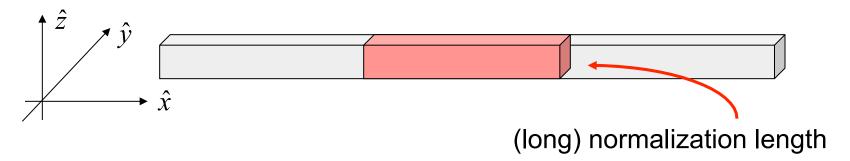
#### one-dimensional electrons



semi-infinite in along the x-direction, but very small in the yand z-directions.

$$\psi(\vec{r}) \sim e^{i\vec{k}\cdot\vec{r}} \rightarrow \sin(k_y y)\sin(k_z z) \times e^{ik_x x}$$

#### one-dimensional electrons



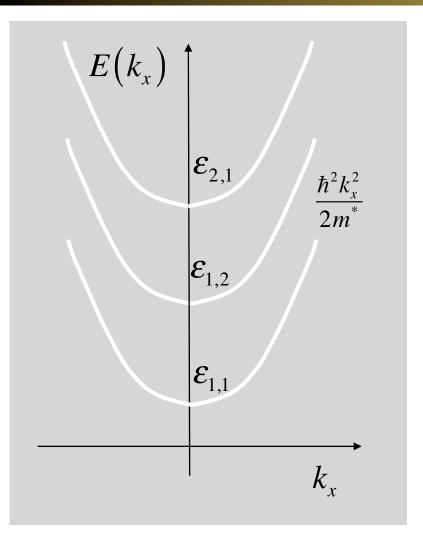
$$\psi(\vec{r}) \sim e^{i\vec{k}\cdot\vec{r}} \rightarrow \sin(k_y y)\sin(k_z z) \times e^{ik_x x}$$

$$\psi(y=0) = \psi(y=t_y) = 0 \qquad \psi(z=0) = \psi(z=t_z) = 0$$

$$k_y t_y = m\pi \qquad k_y = \frac{m\pi}{t_y} \qquad k_z t_z = n\pi \qquad k_z = \frac{n\pi}{t_z}$$

$$\varepsilon_{m,n} = \frac{\hbar^2 m^2 \pi^2}{2m^* t_y^2} + \frac{\hbar^2 n^2 \pi^2}{2m^* t_z^2}$$

## subbands



$$\varepsilon_{m,n} = \frac{\hbar^2 \pi^2}{2m^*} \left( \frac{m^2}{t_y^2} + \frac{n^2}{t_z^2} \right)$$

$$E = \varepsilon_{m,n} + \frac{\hbar^2 k_x^2}{2m^*}$$

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# summary

$$E = E_C + E(k)$$



bottom of band or subband

"dispersion" k in unconfined direction 1D, 2D, 3D

# questions

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